LISTING OF THE CLAIMS:

Claims 1-7 (Cancelled).

8. (Previously Presented) A method of fabricating a semiconductor device, comprising the steps:

providing a semiconductor substrate;

forming a gate dielectric layer on the substrate;

forming a gate stack on said dielectric layer, including the steps of

i) forming a first gate layer on the dielectric layer, and

ii) forming a second gate layer on the first gate layer;

forming a first spacer around the gate stack;

removing the second gate layer,

implanting ions in the first gate layer to form a doped gate above the gate dielectric layer;

after the step of implanting ions in the first gate layer,

removing the first spacer,

forming a second spacer, thinner than the first spacer, around the first gate layer, and

implanting further ions in the semiconductor device, around the second spacer, to form doped source and drain extension regions in the semiconductor device

Claim 9 (Cancelled).

10. (Original) A method according to Claim 8, wherein each of the first gate layer and second gate layer has a height of about 150 nm.

11. (Original) A method according to Claim 8, wherein the first gate layer is comprised of polysilicon.

12. (Original) A method according to Claim 8, wherein the first spacer is comprised of silicon oxide.

Claims 13-18 (Cancelled).